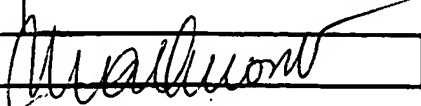


SHEET 1 OF 1

<b>FORM PTO - 1449</b>  <b>SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT</b>				<b>ATTORNEY DOCKET NO.:</b> ASC-049C1  <b>APPLICANT(S):</b> Fitzgerald  <b>SERIAL NO.:</b> 10/774,890  <b>FILING DATE:</b> February 9, 2004  <b>GROUP:</b> 2818				
<b>U.S. PATENT DOCUMENTS</b>								
EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
						FAX RECEIVED		
						JUN 24 2005		
						OFFICE OF PETITIONS		
<b>FOREIGN PATENT DOCUMENTS</b>								
EXAM. INIT.	DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
<b>OTHER ART, JOURNAL ARTICLES, ETC.</b>								
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)							
MH	C102	C. Rosenblad, et al., "Strain relaxation of graded SiGe buffers grown at very high rates," <u>Materials Science and Engineering</u> , B71 (2000), pp. 20-23.						
MH	C103	E.A. Fitzgerald, et al., "Dislocations in Relaxed SiGe/Si Heterostructures," <u>Phys. Stat. Sol.</u> , (a) 171 (1999) pp. 227-238						
EXAMINER					<b>DATE CONSIDERED</b> 07/01/05			